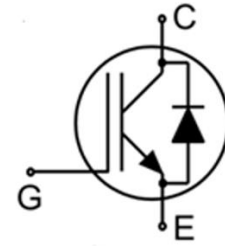


Trench Field-Stop Technology IGBT

Features

- 650V, 75A
- $V_{CE(sat)}(typ.) = 1.80V @ V_{GE}=15V, I_C=75A$
- Maximum Junction Temperature 175°C
- Pb-free Lead Plating; RoHS Compliant



Applications

- Solar Converters
- Uninterrupted Power Supply
- Welding Converters
- Mid to High Range Switching Frequency Converters



Key Performance and Package Parameters

Order codes	V_{CE}	I_C	$V_{CE(sat)}, T_{vj}=25^{\circ}C$	T_{vjmax}	Marking	Package
XD075L065CX1S3	650V	75A	1.80V	175°C	D75L65CX1	TO247-3L

Absolute Maximum Ratings

Symbol	Parameter	Value	Unit
V_{CES}	Collector-Emitter Voltage	650	V
V_{GES}	Gate-Emitter Voltage	±20	V
I_C	Continuous Collector Current ($T_C=25^{\circ}C$)	110	A
	Continuous Collector Current ($T_C=100^{\circ}C$)	75	A
I_{CM}	Pulsed Collector Current (Note 1)	300	A
I_F	Diode Forward Current ($T_C=25^{\circ}C$)	110	A
	Diode Forward Current ($T_C=100^{\circ}C$)	75	A
P_D	Maximum Power Dissipation ($T_C=25^{\circ}C$)	385	W
	Maximum Power Dissipation ($T_C=100^{\circ}C$)	192	W
T_J	Operating Junction Temperature Range	-40 to 175	°C
T_{STG}	Storage Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Max.	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case for IGBT	0.39	°C/W
$R_{\theta JC}$	Thermal Resistance, Junction to Case for Diode	0.41	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	40	°C/W

Electrical Characteristics (T_c=25°C unless otherwise noted.)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV _{CES}	Collector-Emitter Breakdown Voltage	V _{GE} =0V, I _C =200uA	650	---	---	V
I _{CES}	Collector-Emitter Leakage Current	V _{CE} =650V, V _{GE} =0V	---	---	75	uA
I _{GES}	Gate Leakage Current, Forward	V _{GE} =20V, V _{CE} =0V	---	---	100	nA
	Gate Leakage Current, Reverse	V _{GE} =-20V, V _{CE} =0V	---	---	100	nA
V _{GE(th)}	Gate Threshold Voltage	V _{GE} =V _{CE} , I _C =750uA	3.2	4	4.8	V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	V _{GE} =15V, I _C =75A, T _J =25°C	---	1.80	2.20	V
		V _{GE} =15V, I _C =75A, T _J =125°C	---	2.05	---	V
Q _G	Total Gate Charge	V _{CC} =520V	---	118	---	nC
Q _{GE}	Gate-Emitter Charge	V _{GE} =15V	---	32	---	nC
Q _{GC}	Gate-Collector Charge	I _C =75A	---	30	---	nC
t _{d(on)}	Turn-on Delay Time	V _{CC} =400V V _{GE} =±15V I _C =75A R _G =8Ω Inductive Load T _C =25°C	---	32	---	ns
t _r	Turn-on Rise Time		---	91	---	ns
t _{d(off)}	Turn-off Delay Time		---	152	---	ns
t _f	Turn-off Fall Time		---	129	---	ns
E _{on}	Turn-on Switching Loss		---	1.88	---	mJ
E _{off}	Turn-off Switching Loss		---	2.43	---	mJ
E _{ts}	Total Switching Loss		---	4.31	---	mJ
C _{ies}	Input Capacitance	V _{CE} =25V V _{GE} =0V f =1MHz	---	3781	---	pF
C _{oes}	Output Capacitance		---	355	---	pF
C _{res}	Reverse Transfer Capacitance		---	38	---	pF
SCSOA	Short Circuit Safe Operation Area	V _{GE} =15V, V _{CC} ≤400V, T _{J,start} ≤25°C	5	---	---	uS

Diode Characteristics ($T_C=25^{\circ}\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
V_F	Diode Forward Voltage	$I_F=75\text{A}$, $T_J=25^{\circ}\text{C}$	---	1.45	1.75	V
		$I_F=75\text{A}$, $T_J=150^{\circ}\text{C}$	---	1.35	---	V
t_{rr}	Diode Reverse Recovery Time	$V_R=400\text{V}$ $I_F=75\text{A}$ $dI_F/dt=500\text{A/us}$ $T_C=25^{\circ}\text{C}$	---	95	---	ns
I_{rr}	Diode peak Reverse Recovery Current		---	14	---	A
Q_{rr}	Diode Reverse Recovery Charge		---	650	---	nC

Note1: Repetitive rating, pulse width limited by maximum junction temperature

Typical Characteristics

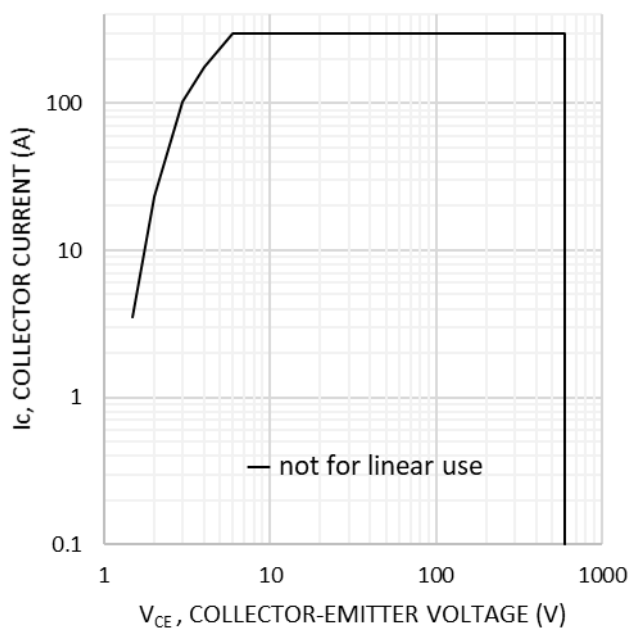


Fig. 1 Forward bias safe operating area (D=0, $T_c=25^\circ\text{C}$, $T_{vj}\leq 175^\circ\text{C}$; $V_{GE}=15\text{V}$. Recommended use at $V_{GE}\geq 7.5\text{V}$)

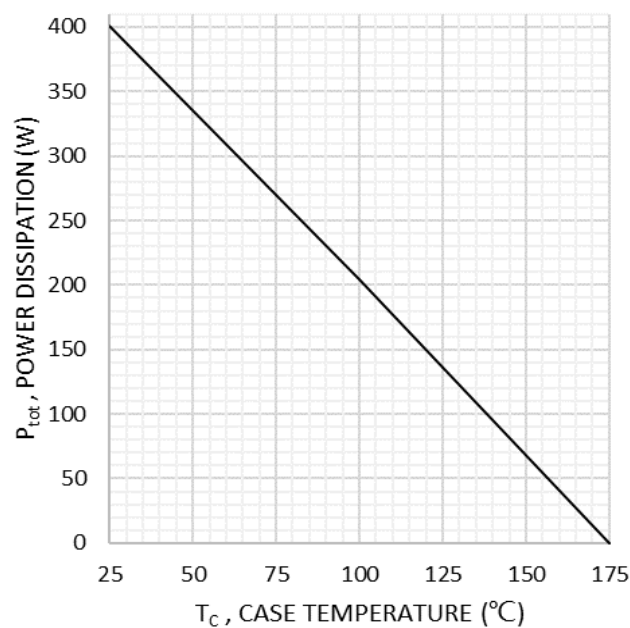


Fig. 2 Power dissipation as a function of case temperature ($T_{vj}\leq 175^\circ\text{C}$)

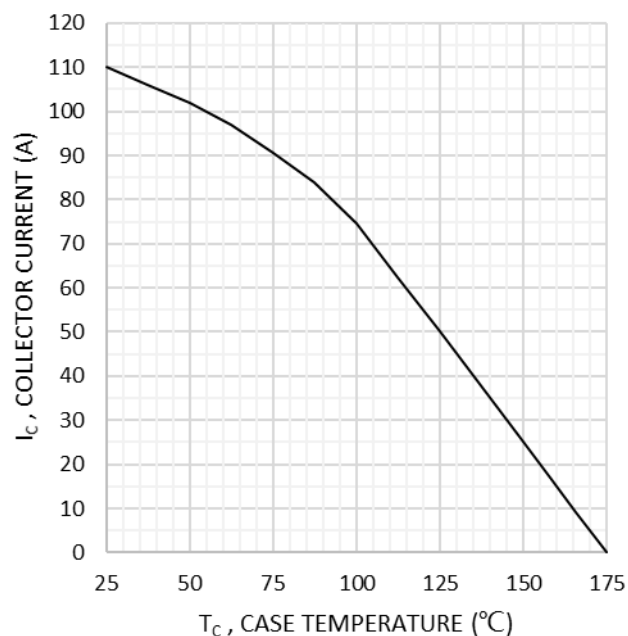


Fig. 3 Collector current as a function of case temperature ($V_{GE}\geq 15\text{V}$, $T_{vj}\leq 175^\circ\text{C}$)

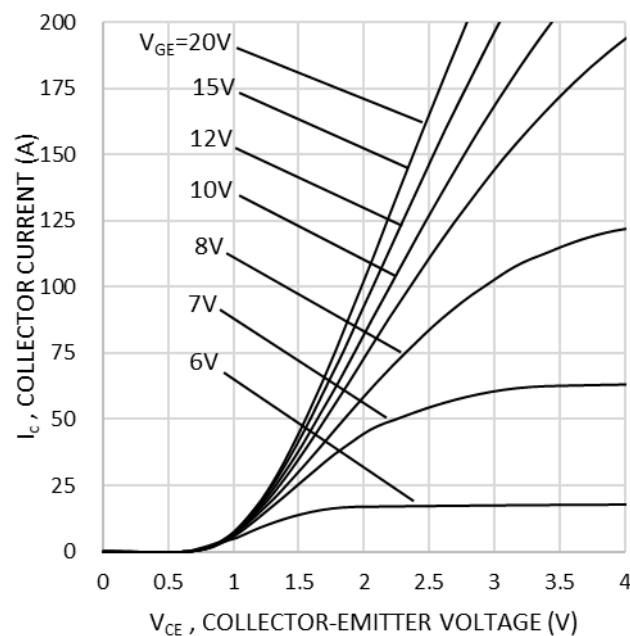


Fig. 4 Typical output characteristic ($T_{vj}=25^\circ\text{C}$)

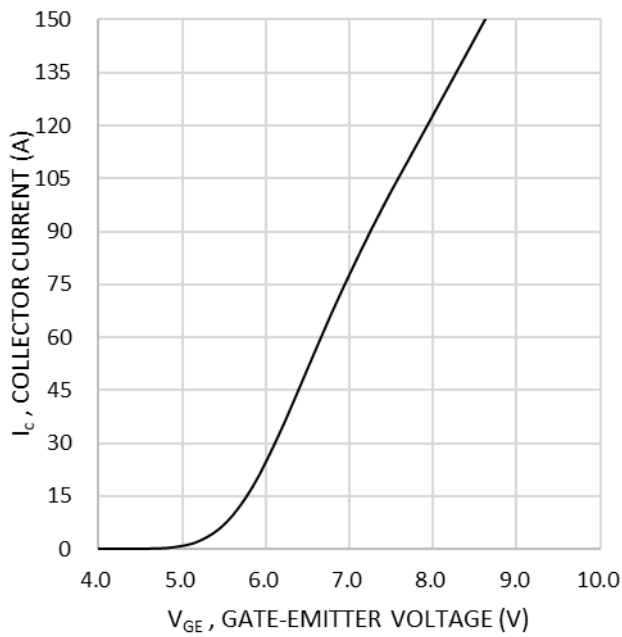


Fig. 5 Typical transfer characteristics ($V_{CE}=20V$)

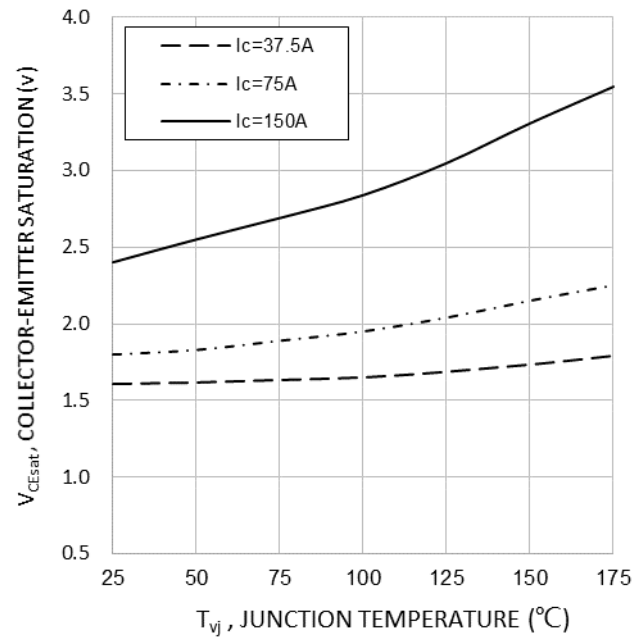


Fig. 6 Typical collector-emitter saturation voltage as a function of junction temperature ($V_{GE}=15V$)

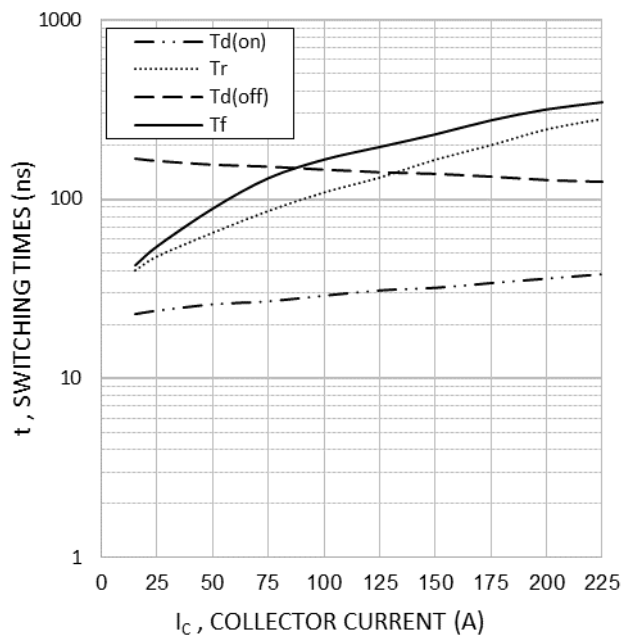


Fig. 7 Typical switching times as a function of collector current (inductive load, $T_{vj}=25^{\circ}C$, $V_{CE}=400V$, $V_{GE}=15/0V$, $r_G=8\Omega$)

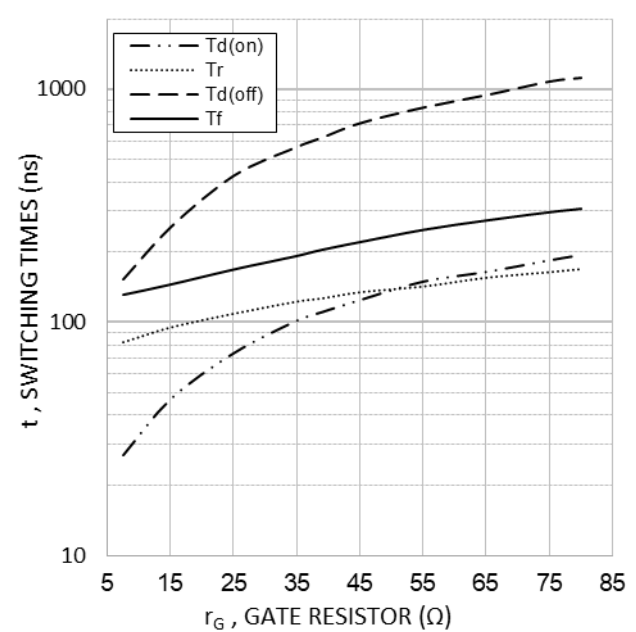


Fig. 8 Typical switching times as a function of gate resistance (inductive load, $T_{vj}=25^{\circ}C$, $V_{CE}=400V$, $V_{GE}=15/0V$, $I_c=75A$)

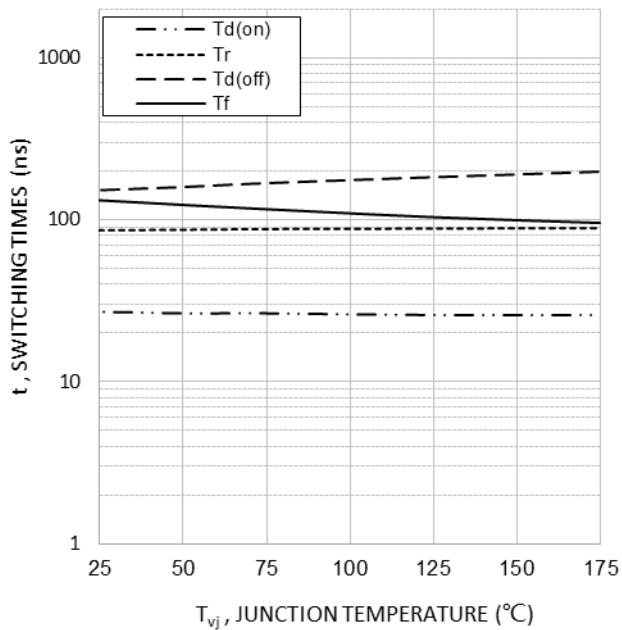


Fig. 9 Typical switching times as a function of junction temperature (inductive load, $V_{CE}=400V$, $V_{GE}=15/0V$, $I_C=75A$, $r_G=8\Omega$)

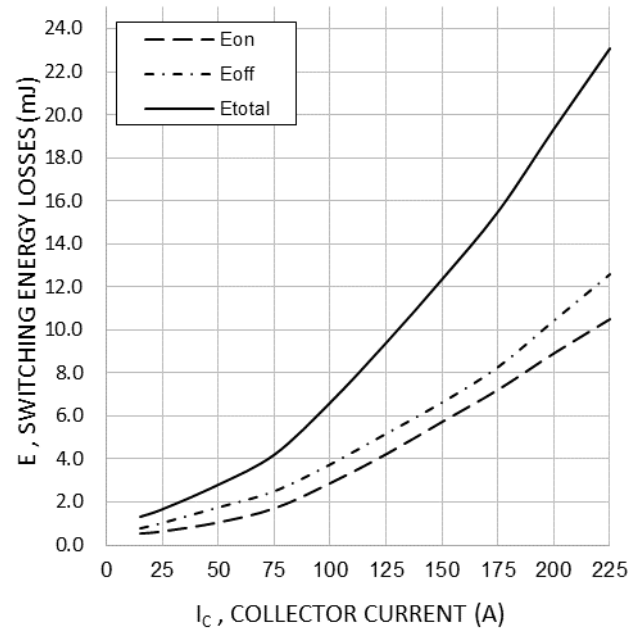


Fig. 10 Typical switching energy losses as a function of collector current (inductive load, $T_{j}=25^{\circ}C$, $V_{CE}=400V$, $V_{GE}=15/0V$, $r_G=8\Omega$)

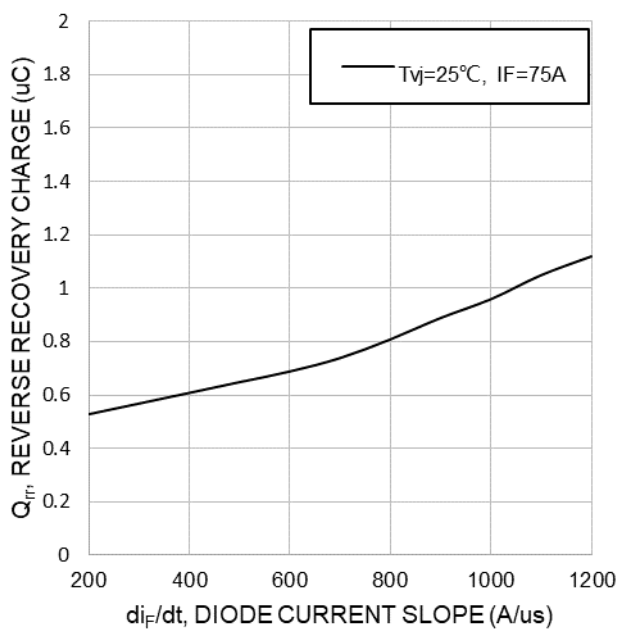


Fig. 11 Typical reverse recovery charge as a function of diode current slope ($V_R=400V$)

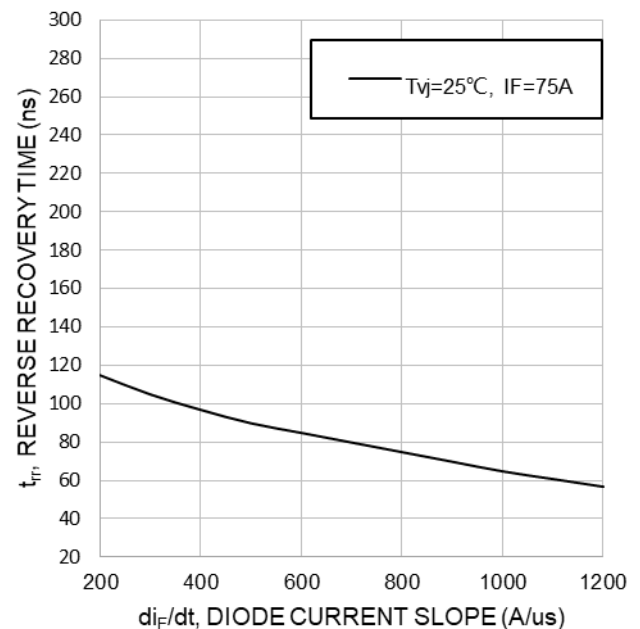


Fig. 12 Typical reverse recovery time as a function of diode current slope ($V_R=400V$)

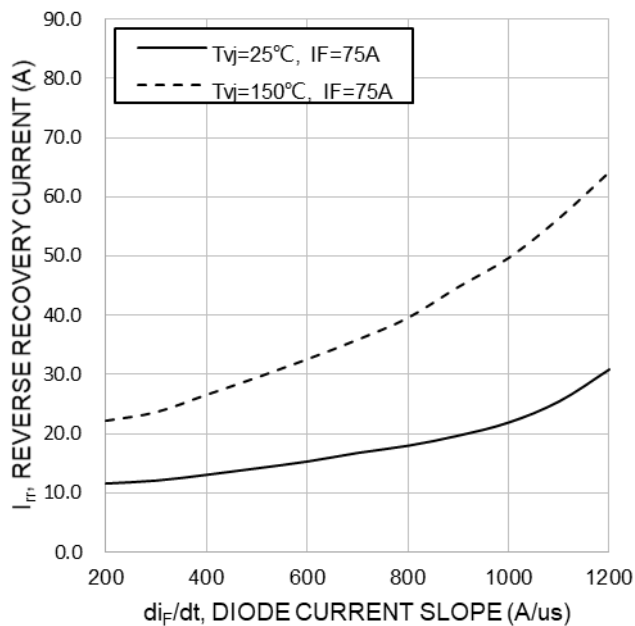


Fig. 13 Typical reverse recovery current as a function of diode current slope ($V_R=400\text{V}$)

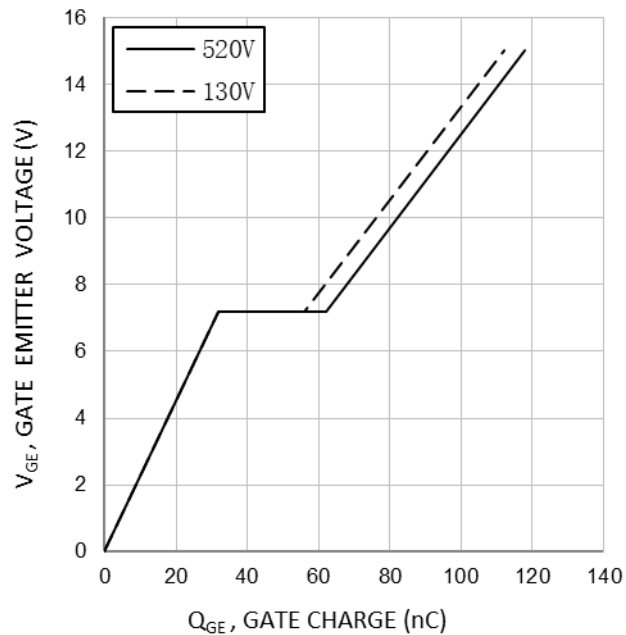


Fig. 14 Typical gate charge ($I_C=75\text{A}$)

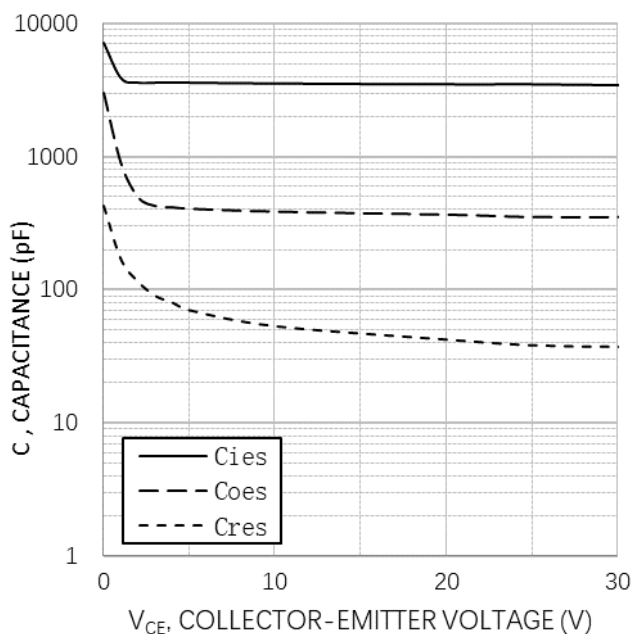


Fig. 15 Typical capacitance as a function of collector-emitter voltage ($V_{GE}=0\text{V}$, $f=1\text{MHz}$)

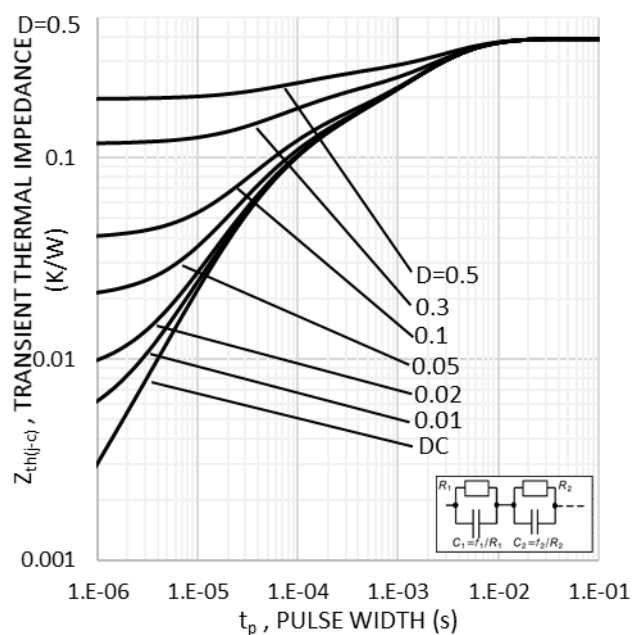
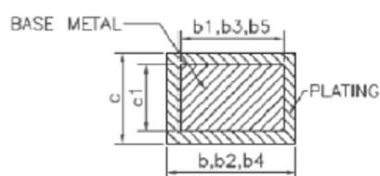
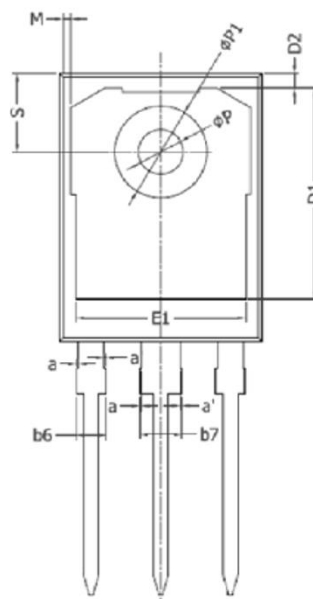


Fig. 16 IGBT transient thermal impedance ($D=t_p/T$)

TO-247-3L



SECTION C-C,D-D & E-E

SYMBOL	MIN	NOM	MAX
A	4.90	5.00	5.10
A1	2.31	2.41	2.51
A2	1.90	2.00	2.10
a	0	---	0.15
a'	0	---	0.15
b	1,16	---	1,26
b1	1,15	1,2	1,22
b2	1,96	---	2,06
b3	1,95	2,00	2,02
b4	2,96	---	3,06
b5	2,96	3,00	3,02
b6	---	---	2,25
b7	---	---	3,25
c	0,59	---	0,66
c1	0,58	0,60	0,62
D	20,90	21,00	21,10
D1	16,25	16,55	16,85
D2	1,05	1,17	1,35
E	15,70	15,80	15,90
E1	13,10	13,30	13,50
E2	4,40	4,50	4,60
E3	1,50	1,60	1,70
e	5,436 BSC		
L	19,80	19,92	20,10
L1	---	---	4,30
M	0,35	---	0,95
P	3,40	3,50	3,60
P1	7,00	---	7,40
P2	2,40	2,50	2,60
Q	5,60	---	6,00
S	6,05	6,15	6,25
T	9,80	---	10,20
U	6,00	---	6,40